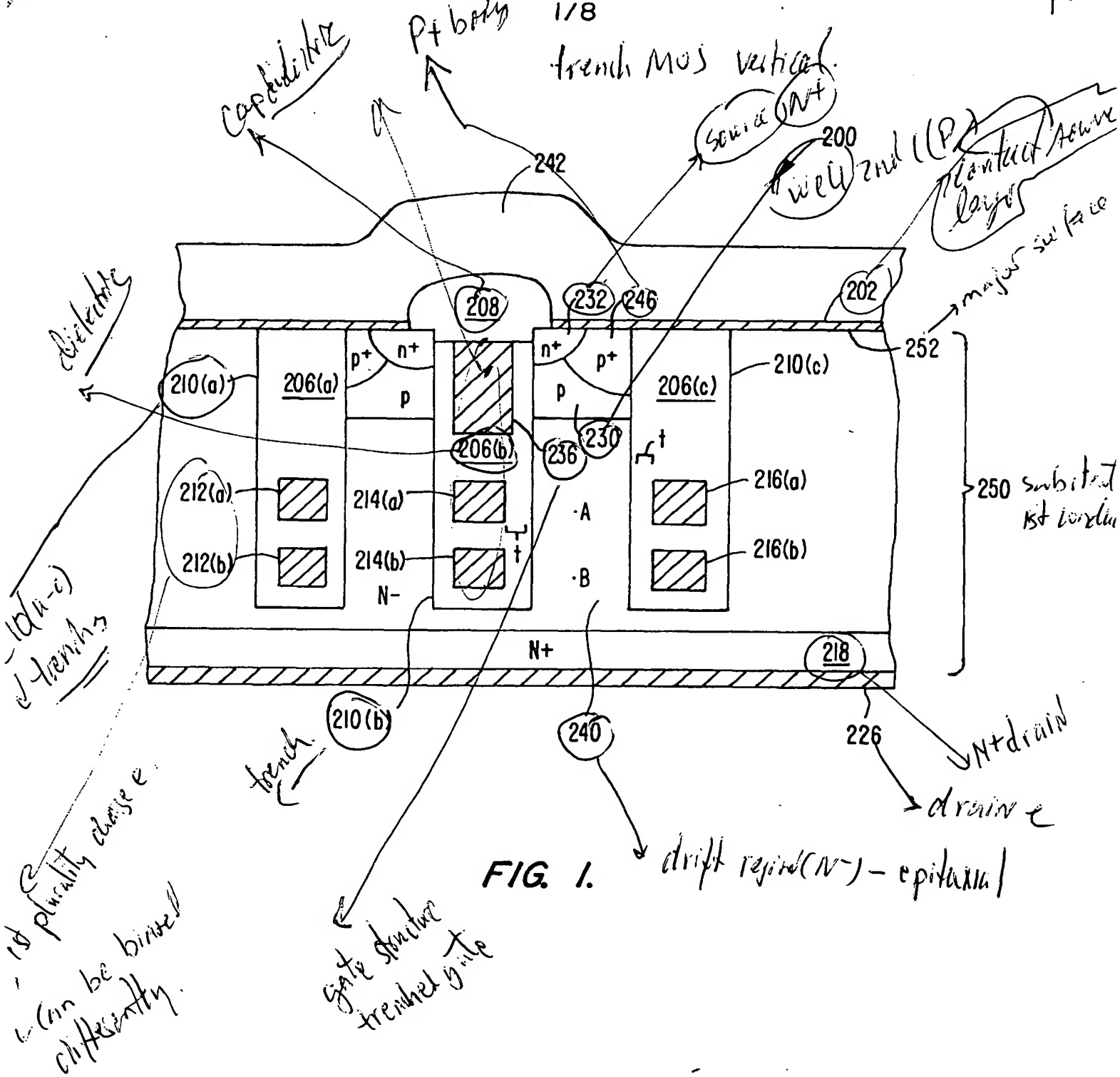
1/8
trench MOS vertical
Pt body
capacitive
source (N+)
200
well 2nd ((P)
contact area
larger
242
208
232
246
202
major surface
252
dielectric
210(a)
206(a)
p+
n+
p
n+
p+
206(c)
210(c)
206(b)
236
230
t
212(a)
214(a)
216(a)
250 substrate
212(b)
214(b)
216(b)
·A
·B
N-
N+
218
210(b)
240
226
N+drain
drain e
trench
1st plurality charge e
(can be biased differently
gate structure trenched gate
drift region(N-) - epitaxial

FIG. 1.